Application

- · Motor drive
- · Inverter, Converter
- · Photovoltaics, wind power generation.
- · Induction heating equipment.

Features

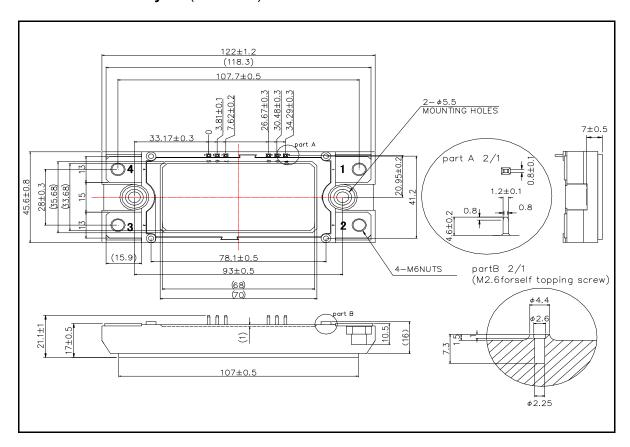
- 1) Low surge, low switching loss.
- 2) High-speed switching possible.
- 3) Reduced temperature dependence.

*Do not connnect to NC pin.

Construction

This product is a half bridge module consisting of SiC-DMOS from ROHM.

●Dimensions & Pin layout (Unit : mm)

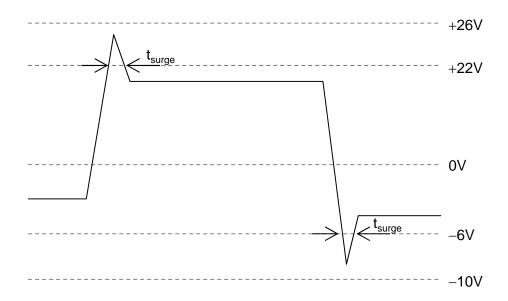


● Absolute maximum ratings (Tj = 25°C)

Parameter	Symbol	Conditions	Limit	Unit
Drain-source voltage	V_{DSS}	G-S short	1200	V
Gate-source voltage(+)	V_{GSS}	D-S short	22	V
Gate-source voltage(-)	V GSS	D-S short	- 6	V
G - S Voltage (tsurge<300ns)	$V_{GSSsurge}$	D-S short	-10 to +26	°C
Drain current *1	I _D	DC(Tc=60°C)	204	Α
	I _{DRM}	Pulse (Tc=60°C) 1ms *2	360	Α
Source current *1	Is	Tc=60°C V _{GS} =18V	204	Α
	I _{SRM}	Pulse (Tc=60°C) 1ms V _{GS} =18V * ²	360	Α
		Pulse (Tc=60°C) 10 μ s V _{GS} =0V * ²	360	Α
Total power disspation *3	Ptot	Tc=25°C	1360	W
Max Junction Temperature	Tjmax		175	°C
Junction Temperature	Tjop		-40 to 150	°C
Storage temperature	Tstg		-40 to 125	°C
Isolation voltage	Visol	Terminals to baseplate, f=60Hz AC 1min. 2500		Vrms
Mounting torque	_	Main Terminals : M6 screw	4.5	N·m
		Mounting to heat shink: M5 screw	3.5	N·m

^(*1) Case temperature (T_c) is defined on the surface of base plate just under the chips.

Example of acceptable V_{GS} waveform



^(*2) Repetition rate should be kept within the range where temperature rise if die should not exceed T_{jmax}.

^(*3) T_i is less than 175°C

●Electrical characteristics (Tj=25°C)

Parameter	Symbol	Conditions		Min.	Тур.	Max.	Unit
Static drain-source on-state voltage	V _{DS(on)}	I _D =180A, V _{GS} =18V	Tj=25°C	-	2.3	3.2	V
			Tj=125°C	-	3.3	4.4	
			Tj=150°C	-	3.6	5	
Drain cutoff current	I _{DSS}	V _{DS} =1200V, V _{GS} =0V		-	-	10	μΑ
Source-drain voltage	V_{SD}	V _{GS} =0V, I _S =180A	Tj=25°C	1	5.4	-	V
			Tj=125°C	1	5.1	-	
			Tj=150°C	1	4.8	ı	
		V _{GS} =18V, I _S =180A	Tj=25°C	1	2.3	-	
			Tj=125°C	1	3.3	-	
			Tj=150°C	1	3.5	-	
Gate-source threshold voltage	$V_{GS(th)}$	V _{DS} =10V, I _D =35.2mA		1.6	2.7	4	V
Gate-source leakage current	I _{GSS}	V_{GS} =22V, V_{DS} =0V		1	-	0.5	μА
		$V_{GS} = -6V, V_{DS} = 0V$		-0.5	-	-	
Switching characteristics	td(on)	V _{GS(on)} =18V, V _{GS(off)} =0V		ı	80	-	ns
	tr	V _{DS} =600V		ı	90	-	
	trr	I _D =180A		1	50	-	
	td(off)	$R_G=5.6\Omega$		1	300	ı	
	tf	inductive load	1	90	-		
Input capacitance	Ciss	V _{DS} =10V, V _{GS} =0V, f=1MHz		1	23	-	nF
Internal gate resistor	R_{Gint}	Tj=25°C		-	1.15	-	Ω
Stray Inductance	Ls			1	25	-	nΗ
Creepage Distance	-	Terminal to heat sink		1	11.5	-	mm
		Terminal to terminal		ı	19.0	-	mm
Clearance Distance	-	Terminal to heat sink		-	9.5	-	mm
		Terminal to terminal		ı	13.0	-	mm
Junction-to-case thermal resistance	Rth(j-c)	DMOS (1/2 module) *4		ı	ı	0.11	°C/W
Case-to-heat sink Thermal resistance	Rth(c-f)	Case to heat sink, per 1 module, Thermal grease applied *5		-	0.035	-	

- (*4) Measurement of Tc is to be done at the point just under the chip.
- (*5) Typical value is measured by using thermally conductive grease of λ=0.9W/(m • K).
- (*6) If the Product is used beyond absolute maximum ratings defined in the Specifications, as its internal structure may be dameged, please replace such Product with a new one.

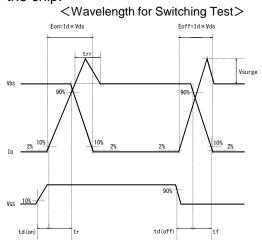


Fig.1 Typical Output Characteristics

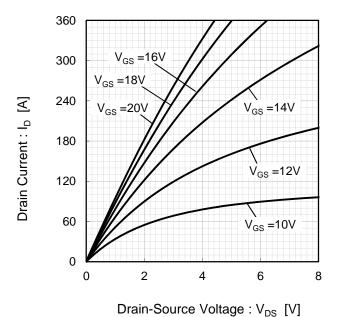


Fig.2 Drain-Source Voltage vs. Drain Current

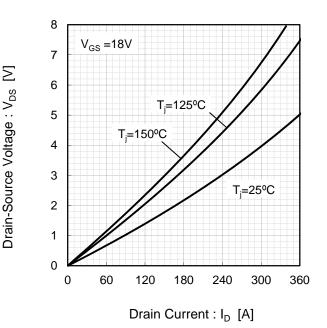
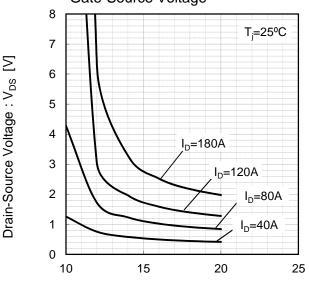
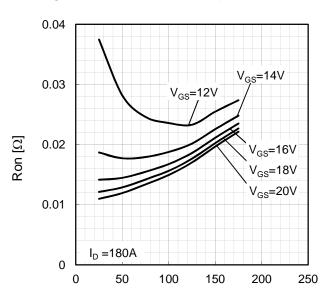


Fig.3 Drain-Source Voltage vs. Gate-Source Voltage



Gate-Source Voltage : V_{GS} [V]

Fig.4 Ron vs Junction Temperature



Junction Temperature : Tj [°C]

Fig.5 Forward characterstic of Diode

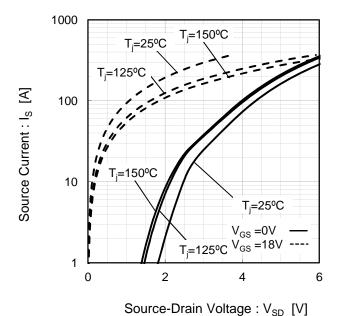
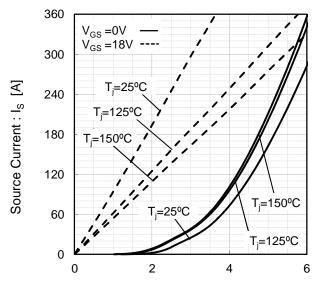


Fig.6 Forward characteristic of Diode



Source-Drain Voltage: V_{SD} [V]

Fig.7 Drain Current vs. Gate-Source Voltage

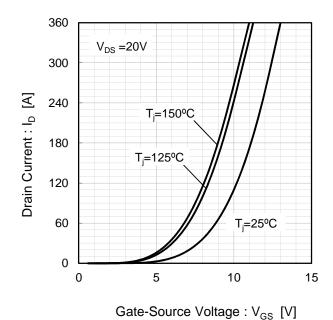
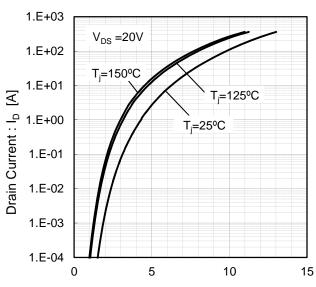


Fig.8 Drain Current vs. Gate-Source Voltage



Gate-Source Voltage : V_{GS} [V]

Fig.9 Switching Characteristics [Tj=25°C]

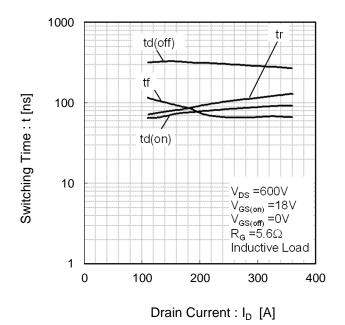


Fig.10 Switching Characteristics [Tj=125°C]

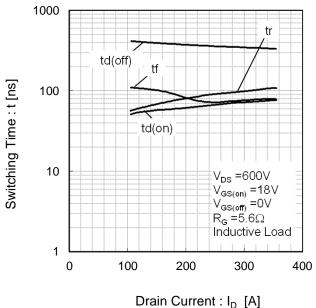


Fig.11 Switching Loss vs. Drain Current [Tj=25°C]

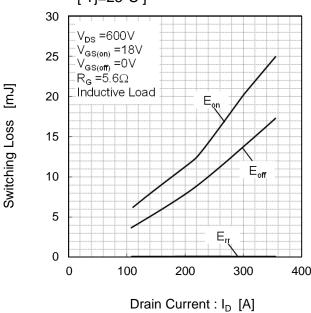
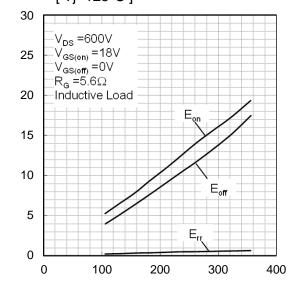
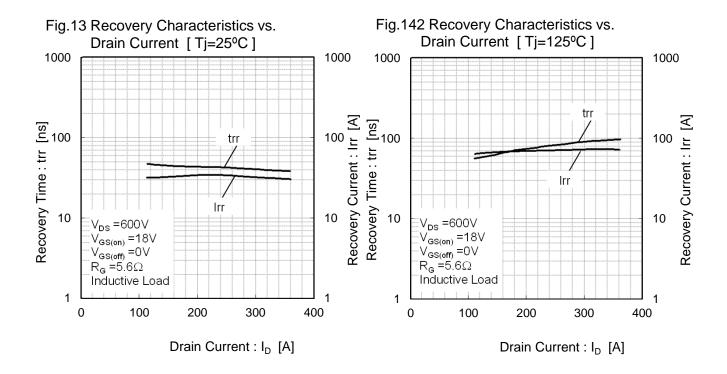


Fig.12 Switching Loss vs. Drain Current [Tj=125°C]



Switching Loss [mJ]



Resistance [Tj=125°C]

10000

V_{DS} =600V

I_D =180A

V_{GS(on)} =18V

V_{GS(off)} =0V

Inductive Load

tf

tr

100

10

10

10

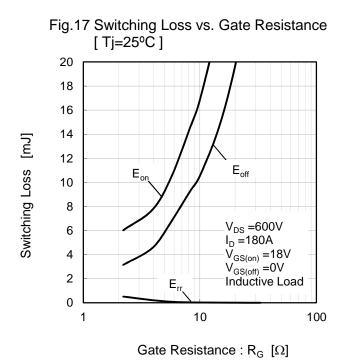
10

100

Gate Resistance : R_G [Ω]

ROHM

Fig.16 Switching Characteristics vs. Gate



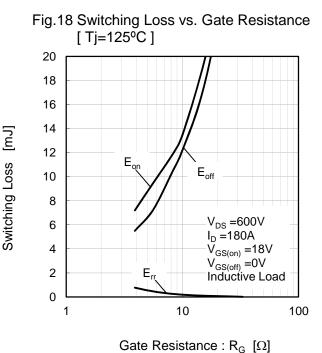


Fig.19 Typical Capacitance vs. Drain-Source Voltage 1.E-07 C_{iss} 1.E-08 Capasitance: C [nF] $\mathsf{C}_{\mathsf{oss}}$ 1.E-09 1.E-10 $\mathsf{C}_{\mathsf{rss}}$ Tj=25°C V_{GS} =0V 1.E-11 1 100 0.01

Drain-Source Voltage : V_{DS} [V]

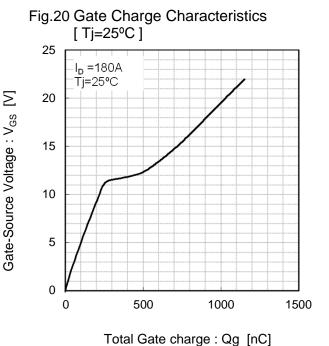
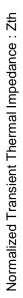
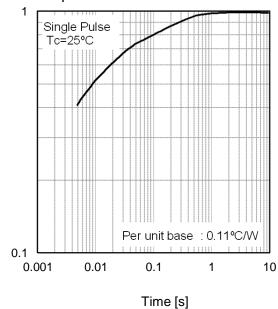


Fig.21 Normalized Transient Thermal Impedance





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